

Title (en)  
Silicon substrate and manufacturing method thereof

Title (de)  
Siliziumsubstrat und Herstellungsverfahren dafür

Title (fr)  
Substrat de silicium et son procédé de fabrication

Publication  
**EP 2096667 B1 20130508 (EN)**

Application  
**EP 09002652 A 20090225**

Priority  
JP 2008049847 A 20080229

Abstract (en)  
[origin: EP2096667A2] A silicon substrate is manufactured from single-crystal silicon which is grown to have a carbon concentration equal to or higher than  $1.0 \times 10^{16}$  atoms/cm<sup>3</sup> and equal to or lower than  $1.6 \times 10^{17}$  atoms/cm<sup>3</sup> and an initial oxygen concentration equal to or higher than  $1.4 \times 10^{18}$  atoms/cm<sup>3</sup> and equal to or lower than  $1.6 \times 10^{18}$  atoms/cm<sup>3</sup> by a CZ method. A device is formed on a front, the thickness of the silicon substrate is equal to or more than 5  $\mu\text{m}$  and equal to or less than 40  $\mu\text{m}$ , and extrinsic gettering which produces residual stress equal to or more than 5 Mpa and equal to or less than 200 Mpa is applied to a back face of the substrate.

IPC 8 full level  
**H01L 21/322** (2006.01); **H01L 21/304** (2006.01); **H01L 21/306** (2006.01)

CPC (source: EP KR US)  
**C30B 15/00** (2013.01 - EP US); **C30B 15/20** (2013.01 - KR); **C30B 29/06** (2013.01 - EP KR US); **H01L 21/30625** (2013.01 - EP KR US); **H01L 21/3221** (2013.01 - EP US); **H01L 21/3225** (2013.01 - EP KR US); **H01L 29/7849** (2013.01 - EP KR US)

Cited by  
FR3122524A1; EP2099073A3; CN110947434A; US10326013B2; US8864907B2; WO2022117804A1

Designated contracting state (EPC)  
FR IT

DOCDB simple family (publication)  
**EP 2096667 A2 20090902**; **EP 2096667 A3 20110615**; **EP 2096667 B1 20130508**; CN 101521199 A 20090902; CN 101521199 B 20120523; JP 2009206431 A 20090910; JP 5568837 B2 20140813; KR 101073419 B1 20111017; KR 20090093854 A 20090902; TW 200944626 A 20091101; TW I395843 B 20130511; US 2009218661 A1 20090903; US 7915145 B2 20110329

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